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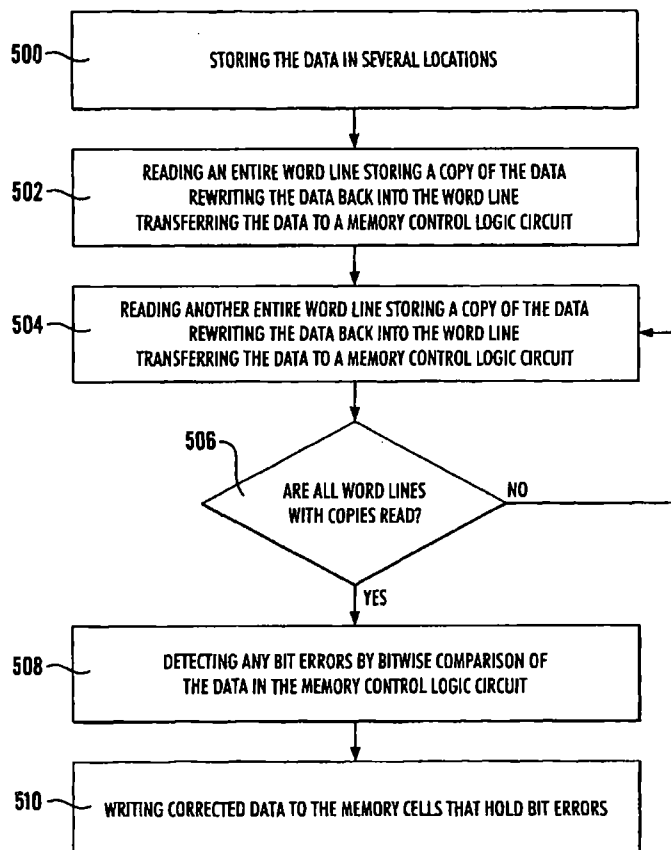
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(54) Title: METHODS FOR STORING DATA IN NON-VOLATILE MEMORIES



(57) Abstract: In methods for storing data in a non-volatile ferroelectric random access memory wherein destructive readout operations are followed by rewrite operations, identical copies of the data are stored in different memory locations that do not have any common word lines or alternative neither common word lines nor common bit lines. A first word line or a segment of a first word line is read in its entirety, said word line or said segment comprising at least a first copy of the identical copies of data. The data thus read are rewritten to the memory location and in addition transferred from the memory location in question to an appropriate cache location, whereafter subsequent memory locations either in the form of word lines or segments thereof are read, and data rewritten to the cache location. The operation is repeated until all identical copies of the data have been transferred to the cache storage. Subsequently bit errors are detected by comparing the identical copies in a memory control logic circuit, which also may be used for caching readout data copies or alternatively be connected with a separate cache memory. Corrected data are written back to the appropriate memory locations holding bit errors when the latter have been detected.

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ACTION

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